Dioda RU3YX BL 2A 100V 50ns DO-15B GALAXY ELECTRICAL

Dane techniczne:
Nazwa: RU3YX
Typ: dioda szybka
Napięcie wsteczne maksymalne: 100V
Prąd przewodzenia: 2A
Czas gotowości: 50ns
Obudowa: DO-15B
Montaż: przewlekany(THT)
Producent: GALAXY ELECTRICAL

BL GALAXY ELECTRICAL

RU3YX(Z) --- RU3C(Z)

HIGH EFFICIENCY RECTIFIER

VOLTAGE RANGE: 100--- 1000 V
CURRENT: 1.1 - 2.0 A

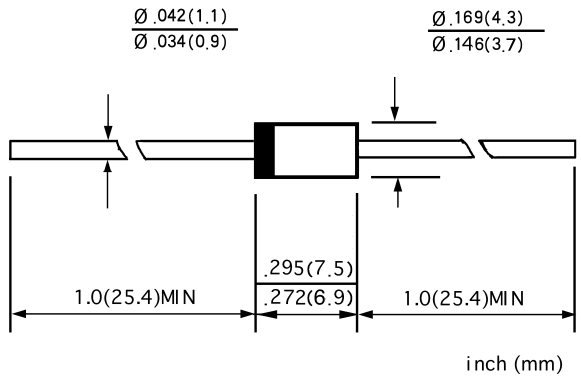
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ Easily cleaned with freon, alcohol, Isopropand and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO-15B, molded plastic
- ◇ Terminals: Axial leads,solderable per MIL-STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.024 ounces, 0.68 grams
- ◇ Mounting: Any

DO - 15B



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		RU3YX	RU3	RU3A	RU3B	RU3C	UNITS
Maximum peak repetitive reverse voltage	V_{RRM}	100	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	100	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	2.0	1.5		1.1	1.5	A
Peak forward surge current 10ms single half-sine-wave superimplsed on rated load @T_J=125℃	I_{FSM}	50.0	20.0				A
Maximum instantaneous forward voltage @ I_F=$I_{F(AV)}$	V_F	0.95	1.5			2.5	V
Maximum reverse current @T_A=25℃	I_R	10.0					μA
at rated DC blocking voltage @T_A=100℃		300.0	400.0				
Maximum reverse recovery time (Note1)	t_{rr}	50	100				ns
Typical junction capacitance (Note2)	C_J	50		30			pF
Typical thermal resistance (Note3)	$R_{\theta JL}$	12					℃/W
Operating junction temperature range	T_J	- 55 ----- + 150					℃
Storage temperature range	T_{STG}	- 55 ----- + 150					℃

NOTE: 1.Measured with I_F=0.5A, I_R=1A, I_{rr}=0.25A

2. Measured at 1.0MH_Z and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient.

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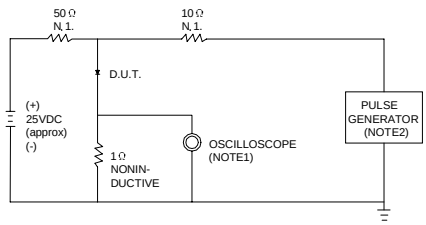
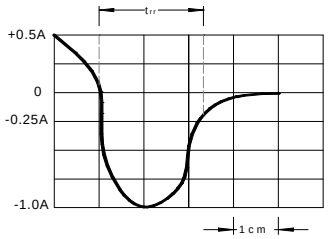
FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC





NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE =1MΩ. 22pF.
2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 Ω.

SET TIME BASE FOR 10/20 ns/cm

FIG.2 – TYPICAL FORWARD CHARACTERISTIC

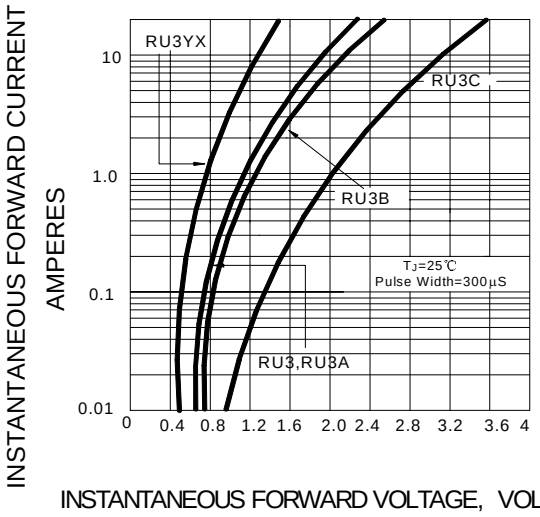


FIG.3 – FORWARD DERATING CURVE

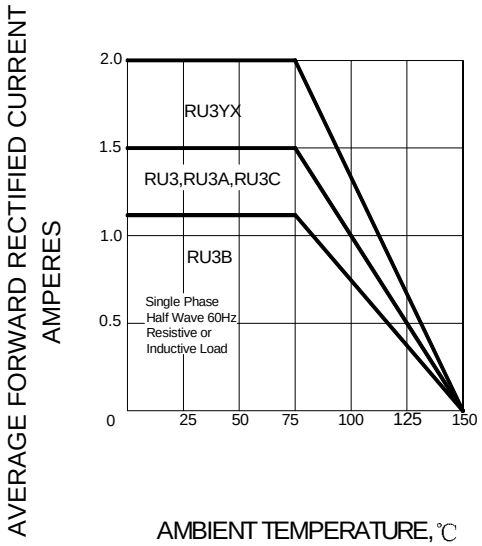


FIG.4 – PEAK FORWARD SURGE CURRENT

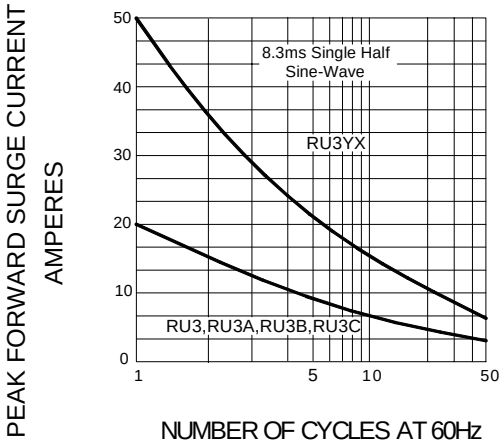


FIG.5--TYPICAL JUNCTION CAPACITANCE